

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	((substrate wafer) and (implant\$3 dop\$3) and (anneal\$3 heat\$3) and (grad\$3 same (SiGe (silicon near5 germanium)) and (crystal near5 lattice) and relax\$3 and (concentration near5 (germanium "Ge")))). clm.	US-PGPU B	OR	ON	2006/09/02 18:52
L2	9	((substrate wafer) and (implant\$3 dop\$3) and (anneal\$3 heat\$3) and (grad\$3 same (SiGe (silicon near5 germanium)) and relax\$3 and (concentration near5 (germanium "Ge")))). clm.	US-PGPU B	OR	ON	2006/09/02 18:52

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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	284	(graded near10 silicon near10 germanium)	US-PGPU B; USPAT; USOCR	OR	ON	2006/09/02 18:42
L2	168	1 and (concentration near5 (germanium "Ge"))	US-PGPU B; USPAT; USOCR	OR	ON	2006/09/02 18:43
L3	147	(graded and (SiGe (silicon near5 germanium)))	FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/02 18:43
L4	24	3 and (concentration same (germanium "Ge"))	FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/02 18:43